

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions
and listings of claims in the application:

Listing of Claims:

1 1. (Previously Amended) A semiconductor device
2 including an input circuit or an output circuit configured
3 with a plurality of first MOS transistors in a first area
4 of a principal plane on a semiconductor substrate, and an
5 internal circuit configured with a plurality of second MOS
6 transistors in a second area of the principal plane on the
7 semiconductor substrate,
8 wherein a first voltage is applied to said plurality
9 of first MOS transistors,
10 wherein a second voltage smaller than said first
11 voltage is applied to said plurality of second MOS
12 transistors,
13 wherein a gate length of a first gate electrode of
14 said plurality of first MOS transistors is larger than a
15 gate length of a second gate electrode of said plurality of
16 second MOS transistors, and

17 wherein a spacing between said first gate electrode of
18 the first MOS transistors and a first contact hole for
19 connecting a wiring to a source region or a drain region of
20 the first MOS transistors is larger than a spacing between
21 said second gate electrode and a second contact hole for
22 connecting a wiring to a source region or a drain region of
23 the second MOS transistors.

1 2. (Previously Amended) A semiconductor device
2 including an input circuit or an output circuit configured
3 with a plurality of first MOS transistors in a first area
4 of a principal plane on a semiconductor substrate, and an
5 internal circuit configured with a plurality of second MOS
6 transistors in a second area of the principal plane on the
7 semiconductor substrate,
8 wherein a first voltage is applied to said plurality
9 of first MOS transistors,
10 wherein a second voltage smaller than said first
11 voltage is applied to said plurality of second MOS
12 transistors,
13 wherein a gate length of a first gate electrode of
14 said plurality of first MOS transistors is larger than a

15 gate length of a second gate electrode of said plurality of
16 second MOS transistors, and

17 wherein a spacing between an edge of a first active
18 region in which the first MOS transistors are formed and a
19 first contact hole for connecting a wiring to a source
20 region or a drain region of the first MOS transistors is
21 larger than a spacing between an edge of a second active
22 region in which the second MOS transistors are formed and a
23 second contact hole for connecting a wiring to a source
24 region or a drain region of the second MOS transistors.

1 3. (Previously Amended) A semiconductor device
2 according to Claim 1,

3 wherein said input circuit or said output circuit
4 operates with said first voltage, and

5 wherein said internal circuit operates with said
6 second voltage.

1 4. (Previously Amended) A semiconductor device
2 according to Claim 1,

3 wherein said plurality of first MOS transistors are
4 first voltage withstanding MOS transistors, and

5 wherein said plurality of second MOS transistors are
6 second voltage withstanding MOS transistors.

1 5. (Previously Amended) A semiconductor device
2 according to Claim 1,
3 wherein a gate insulating film thickness of the first
4 MOS transistors is larger than a gate insulating film
5 thickness of the second MOS transistors.

1 6. (Previously Amended) A semiconductor device
2 according to Claim 1,
3 wherein an area of the active region in which the
4 first MOS transistors are formed is larger than an area of
5 the active region in which the second MOS transistors are
6 formed.

1 7. (Previously Amended) A semiconductor device
2 according to Claim 1,
3 wherein said plurality of first MOS transistors are p-
4 channel type, and the source of each of said plurality of
5 first MOS transistors is supplied with said first voltage,
6 and

7 wherein said plurality of second MOS transistors are
8 p-channel typ , and the source of each of said plurality of
9 second MOS transistors is supplied with said second
10 voltage.

8-20 (Cancelled)

1 ~~21.~~ (Previously Amended) A semiconductor device
2 according to Claim 2,
3 wherein said input circuit or said output circuit
4 operates with said first voltage, and wherein said internal
5 circuit operates with said second voltage.

1 ~~22.~~ (Previously Amended) A semiconductor device
2 according to Claim 2,
3 wherein said plurality of first MOS transistors are
4 first voltage withstanding MOS transistors, and
5 wherein said plurality of second MOS transistors are
6 second voltage withstanding MOS transistors.

1 ~~23.~~ (Previously Amended) A semiconductor device
2 according to Claim 2,

3 wherein a gate insulating film thickness of the first
4 MOS transistors is larger than a gate insulating film
5 thickness of the second MOS transistors.

1 14. (Previously Amended) A semiconductor device
2 according to Claim 2,

3 wherein an area of the active region in which the
4 first MOS transistors are formed is larger than an area of
5 the active region in which the second MOS transistors are
6 formed.

1 12. (Previously Amended) A semiconductor device
2 according to Claim 2,

3 wherein said plurality of first MOS transistors are p-
4 channel type, and the source of each of said plurality of
5 first MOS transistors is supplied with said first voltage,
6 and

7 wherein said plurality of second MOS transistors are
8 p-channel type, and the source of each of said plurality of
9 second MOS transistors is supplied with said second
10 voltage.

26. (Cancel d)